

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	124	(IGFET or insulated near gate near field near effect near transistor) and (two near group Iv near elements)	USPAT ; JPO; DERWE NT	2001/09/2 5 10:57
2	BRS	L2	3	257/290 and 257/412	USPAT ; JPO; DERWE NT	2001/09/2 5 10:02
3	BRS	L3	7	257/291 and 257/412	USPAT ; JPO; DERWE NT	2001/09/2 5 10:03
4	BRS	L4	1	257/292 and 257/412	USPAT ; JPO; DERWE NT	2001/09/2 5 10:04
5	BRS	L5	2	257/293 and 257/412	USPAT ; JPO; DERWE NT	2001/09/2 5 10:05
6	BRS	L6	3	257/294 and 257/412	USPAT ; JPO; DERWE NT	2001/09/2 5 10:05
7	BRS	L7	1062	257/412	USPAT ; JPO; DERWE NT	2001/09/2 5 10:41
8	BRS	L8	81	(IGFET or insulated near gate near field near effect near transistor) and L7	USPAT ; JPO; DERWE NT	2001/09/2 5 10:07